

ABSTRACT

The present invention relates to a semiconductor device production method including a first die bonding step in which a first semiconductor element is electrically connected to a substrate with a first wire therebetween, a lamination step in which a film-shaped adhesive having a shear stress relaxation rate of 40 to 85% at 100°C after 0.1 seconds is attached to one surface of a second semiconductor element having a larger area than the first semiconductor element, and a second die bonding step in which the second semiconductor element to which the film-shaped adhesive is attached is disposed so that the film-shaped adhesive covers the first semiconductor element, the film-shaped adhesive is press-bonded, and thus the first wire and the first semiconductor element are embedded in the film-shaped adhesive.